

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	13	365/230.05,177,154,156,190,202.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/31 16:29
L5	415	(current adj path\$1) same ((field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 17:08
L6	11	365/230.05,177,154,156,190,202.ccls. and (current adj path\$1) same ((field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:31
L7	11	365/230.05,177,154,156,190,202.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (current adj path\$1) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:35
L8	49	"365"/\$.ccls. and (current adj path\$1) same ((field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:35
L9	15	365/230.05,177,154,156,190,202,185.33,185.23,185.24.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (current adj path\$1) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:42
L10	17	365/230.05,177,154,156,190,202,185.33,185.23,185.24.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (current adj path\$1) same parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 17:05
L14	10	(current adj path\$1) same ((field near2 effect near2 transistor\$1) or FET) same parallel same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 17:09
S1	695	((field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/29 19:33

S2	68	"365"/\$.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:24
S3	3	("5289401" "5400273" "5430670").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/18 12:14
S4	5	("4545036" "4669065" "4734890" "4873664" "5297084").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/02/18 12:17
S5	68	"365"/\$.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (reference with electrode) same (reference with potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:25
S6	27	"365"/\$.ccls. and ((first near2 second near2 field near2 effect near2 transistor\$1) or FET) same (reference with electrode) same (reference with potential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 13:25
S7	2	("5373477" "5463588").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/10 13:28
S8	3	("4366555" "4425632" "4592021").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/10 13:29
S9	3	("3798616" "3975718" "3997881").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/10 13:51
S10	333	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 10:58
S11	317	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode) and ((third near2 fourth near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 06:54

S12	14	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)) and ((third near2 fourth near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)) and ((fifth near2 sixth near2 field near2 effect near2 transistor\$1) or FET) same (word adj2 line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:08
S13	1	("5389559").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 06:56
S14	5	("4545036" "4669065" "4734890" "4873664" "5297084").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 07:00
S15	3	("4366555" "4425632" "4592021").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 07:01
S16	4	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with (reference adj2 potential) with (reference adj2 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 09:52
S17	205	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 08:18
S18	28	"365"/\$.ccls. and ((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:21
S19	205	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 10:58
S20	6	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd) same (word adj2 line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:24

S23	202	((third near2 fourth near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 08:07
S24	2	((third near2 fourth near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd) and (sixth near2 field near2 effect near2 transistor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:27
S25	5	("4545036" "4669065" "4734890" "4873664" "5297084").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 07:49
S28	3	((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd) same transfer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:54
S29	3	("5237395" "5532178" "5689133").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 07:54
S30	286	(drive adj2 transistor\$1) and (transfer adj2 gate adj2 transistor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 07:56
S35	14	(drive adj2 transistor\$1) and ((reference adj2 electrode) or vdd) and ((reference adj2 potential) or vss) and (transfer adj2 gate adj2 transistor\$1) and (wordline or (word adj2 line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 08:00
S38	49	((field near2 effect near2 transistor\$1) or FET) and ((reference adj2 potential) or vss) and ((reference adj2 electrode) or vdd) and (drive adj2 transistor\$1) and (transfer adj2 gate adj2 transistor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 08:20
S39	11	("4176289" "4406957" "5151616" "5153467" "5229659" "5287312" "5359240" "5383158" "5406140" "5410508" "5677641").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 08:26

S40	11	("4176289" "4406957" "5151616" "5153467" "5229659" "5287312" "5359240" "5383158" "5406140" "5410508" "5677641").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 09:50
S41	1794	365/154.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 09:51
S42	772	365/230.05.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/12 14:32
S43	173003	((field near2 effect near2 transistor\$1) or FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 09:53
S44	122	S42 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 09:53
S45	1653	SRAM near9 (6-transistor\$1 or "six")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 09:54
S46	30	S42 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 10:06
S47	10	S44 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 09:55
S48	568	S41 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 10:07
S49	223	S41 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 10:07

S50	73	S43 and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 10:07
S51	4	("5365475" "5923582" "6041008" "6128218").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 10:08
S52	13	("5020029" "5153852" "5222039" "5452246" "5461713" "5471421" "5583821" "5732015" "5790452" "5790461" "5828597" "5837573" "5939762").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 10:09
S53	3	("4779230" "4939693" "4995000").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/11 12:59
S54	114427	((field near2 effect near2 transistor\$1) or FinFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:12
S55	585827	(SRAM near9 (6-transistor\$1) or "six")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:13
S56	9401	S54 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:14
S57	223	S56 and 365/230.05,154,156.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:28
S58	9	365/230.05,177,154.ccls. and ((field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/14 10:57
S59	7	365/230.05,177,154,156,190,202. ccls. and ((first near2 second near2 field near2 effect near2 transistor\$1) or FET) same (reference with potential) same (reference with electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 10:58

S60	6	365/156,230.05,177,154,190,202. ccls. and ((first near2 second near2 field near2 effect near2 transistor\$1) or FET) with ((reference adj2 potential) or vss) with ((reference adj2 electrode) or vdd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 11:14
S61	47	Nowak.in. and FINFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 11:17
S62	8	Nowak.in. and FINFET and SRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 11:17
S63	21	("3603848" "4768076" "4857986" "4933298" "5293052" "5317175" "5497019" "5666311" "5698893" "5729045" "5858841" "5945690" "5960271" "5970330" "6064090" "6121651" "6164781" "6190949" "6194273" "6261886" "6300182").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/14 11:16
S64	415	((field near2 effect near2 transistor\$1) or FET) same (current adj path\$1) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:32
S65	234	(current adj path\$1) same (first near2 second near3 (field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:31
S66	22	"365"/\$.ccls. and (current adj path\$1) same (first near2 second near3 (field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/29 20:14
S67	2	"365"/\$.ccls. and (current adj path\$1) same (first near2 second near3 (field near2 effect near2 transistor\$1) or FET) same parallel with end with (current adj path)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/29 20:14

S68	7	365/156,230.05,177,154,190,202. ccls. and (current adj path\$1) same (first near2 second near3 (field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/29 20:15
S69	7	365/156,230.05,177,154,190,202. ccls. and (current adj path\$1) same (first near2 second near3 (field near2 effect near2 transistor\$1) or FET) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/31 16:26